



HVGT High voltage silicon rectifier is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

SHAPE DISPLAY:



FEATURES:

1. High reliability design.
2. High voltage design.
3. Power frequency ratio.
4. Conform to RoHS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

1. Ignition device power supply.
2. Microwave emission power.
3. General purpose high voltage rectifier.

MECHANICAL DATA:

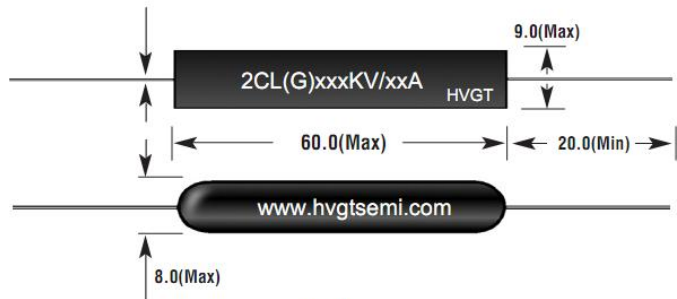
1. Case: epoxy resin molding.
2. Terminal: external lead.
3. Net weight: 7.0 grams (approx).

SIZE: (Unit:mm)

HVGT NAME: HVS-080960H

HVS-080960H Series

Lead Diameter 1.0mm



Unit:mm

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MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	V_{RRM}	$T_a=25^{\circ}C$;	80	kV
Average Output Current	I_F	$T_a=25^{\circ}C$;Resistive Load	100	mA
Suege Current	I_{FSM}	$T_a=25^{\circ}C$;8.3 mS	3.0	A
Junction Temperature	T_J		-40~+125	$^{\circ}C$
Allowable Operation Case Temperature	T_c		125	$^{\circ}C$
Storage Temperature	T_{STG}		-40~+125	$^{\circ}C$

ELECTRICAL CHARACTERISTICS: $T_a=25^{\circ}C$ (Unless otherwise specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V_F	at $25^{\circ}C$; $I_F = I_{F(AV)}$	96	V
Maximum Reverse Current	I_{R1}	at $25^{\circ}C$; $V_R = V_{RRM}$	5.0	μA
	I_{R2}	at $100^{\circ}C$; $V_R = V_{RRM}$	50	μA
Maximum Reverse Recovery Time	T_{RR}	at $25^{\circ}C$; $I_F=0.5I_R$; $I_R=I_{FAVM}$; $I_{RR}=0.25I_R$	--	nS
Junction Capacitance	C_J	at $25^{\circ}C$; $V_R=0V$; $f=1MHz$	--	pF